## **40V N-Channel Enhancement Mode MOSFET**

Voltage

90A Current

### **Features**

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@20A < 5.5m\Omega$
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@4.5V, I<sub>D</sub>@10A<7.5mΩ

40 V

- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

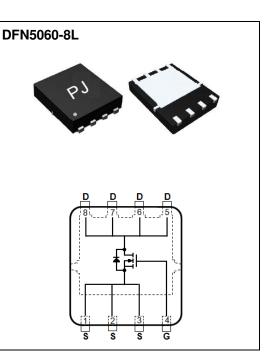
### **Mechanical Data**

- Case : DFN5060-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0028 ounces, 0.08 grams

### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	40	Ň	
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V	
Continuous Drain Current	T <sub>C</sub> =25°C	- I <sub>D</sub> -	90	A	
	$T_{C}=100^{\circ}C$		57		
Pulsed Drain Current <sup>(Note 1)</sup>	T <sub>C</sub> =25°C	I <sub>DM</sub>	240		
Power Dissipation	T <sub>C</sub> =25°C	D-	83	w	
	T <sub>C</sub> =100°C	PD	33		
Continuous Drain Current	T <sub>A</sub> =25°C		14	A	
	T <sub>A</sub> =70°C	Ι <sub>D</sub>	11		
Power Dissipation	T <sub>A</sub> =25°C	D-	2.0	w	
Power Dissipation	T <sub>A</sub> =70°C	PD	1.3		
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{\theta JC}$	1.51	°C/W	
	Junction to Ambient	$R_{\thetaJA}$	62.5		

Limited only By Maximum Junction Temperature









### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
	STINDUL	TEST CONDITION	IVIIIN.	ITF.			
Static		1	1			1	
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}$ =0V, $I_{D}$ =250uA	40	-	-	v	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	1	1.7	2.5	v	
Drain-Source On-State Resistance	$R_{\text{DS(on)}}$	$V_{GS}$ =10V, $I_{D}$ =20A	-	4.2	5.5	- m0	
		$V_{GS}$ =4.5V, $I_{D}$ =10A	-	5.3	7.5	mΩ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =40V, $V_{GS}$ =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	Qg	$V_{DS}$ =32V, I <sub>D</sub> =10A, $V_{GS}$ =4.5V <sup>(Note 2,3)</sup>	-	25	-	nC	
Gate-Source Charge	$Q_{gs}$		-	7	-		
Gate-Drain Charge	$Q_gd$		-	10	-		
Input Capacitance	Ciss		-	1258	-	pF	
Output Capacitance	Coss	$V_{DS}=25V, V_{GS}=0V,$	-	134	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	88	-		
Turn-On Delay Time	td <sub>(on)</sub>		-	18	-	ns	
Turn-On Rise Time	tr	V <sub>DS</sub> =20V, I <sub>D</sub> =1A, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω (Note 2,3)	-	13	-		
Turn-Off Delay Time	td <sub>(off)</sub>		-	109	-		
Turn-Off Fall Time	t <sub>f</sub>		-	73	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			-	-	90	Α	
Diode Forward Current	I <sub>S</sub>						
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.7	1	V	

NOTES :

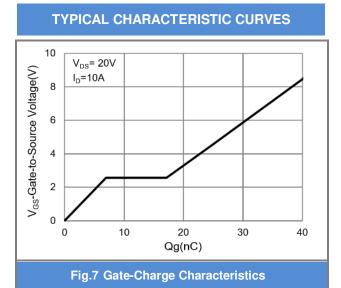
- 1. Pulse width</br>200us, Duty cycle2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150$  °C. Ratings are based on low frequency and duty cycles to keep initial  $T_J = 25$  °C.
- 4. The maximum current rating is package limited.
- 5.  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I\_{AS}=38A, V\_{DD}=25V, V\_{GS}=10V, Starting T\_J=25^{\circ}C.
- 7. Guaranteed by design, not subject to production testing.



#### **PJQ5442 TYPICAL CHARACTERISTIC CURVES** 200 20 V<sub>GS</sub>=10V,8V,6V,5V4.5V V<sub>DS</sub>=5V I<sub>DS</sub>-Drain-to-S ource Current(A) V<sub>GS</sub>=4V I<sub>DS</sub>-Drain-to-S ource Current(A) 150 15 V<sub>GS</sub>=3.5V 100 10 V<sub>GS</sub>=3V T\_=125℃ T,=25℃ 50 5 V<sub>GS</sub>=2.5V 0 0 0 2 3 5 1 4 0 1 3 4 5 2 V<sub>DS</sub>- Drain-to-Source Voltage(V) V<sub>GS</sub>-Gate-to-Source Voltage(V) **Fig.1 On-Region Characteristics Fig.2 Transfer Characteristics** 8 2.5 R<sub>Ds</sub>(on)- On-Resistance (Normalized) $R_{DS}(on)$ - On-Resistance(m $\Omega$ ) 7 2.0 V<sub>GS</sub>=10V, I<sub>D</sub>=20A V<sub>GS</sub>= 4.5V 6 1.5 V<sub>GS</sub>=4.5V, I<sub>D</sub>=10A 1.0 5 V<sub>GS</sub>= 10V 0.5 4 0 25 50 75 100 125 150 175 0 5 10 15 20 Temperature (°C) I<sub>DS</sub>-Drain-to-Source Current(A) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction temperature 20 I<sub>D</sub>=10A 10 I<sub>SD</sub>-Source to Drain Current(A) R<sub>DS</sub>(on)- On-Resistance(mΩ) 15 1 10 T<sub>j</sub>=125°C T<sub>I</sub>=125℃ т<sub>i</sub>=25°С 0.1 T₁=25°C 5 0 0.01 2 4 6 8 10 0 0.3 0.6 0.9 1.2 V<sub>GS</sub>-Gate-to-Source Voltage(V) V<sub>SD</sub>-Source-to-Drain Voltage(V)

Fig.5 On-Resistance Variation with V<sub>GS</sub>

**Fig.6 Body Diode Characteristics** 



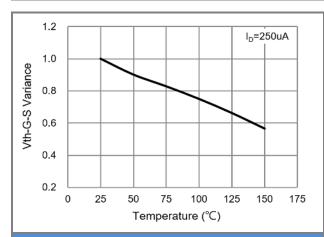
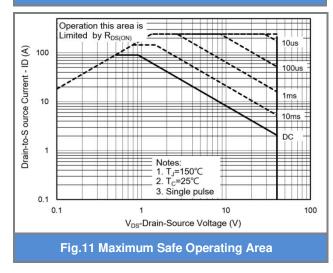
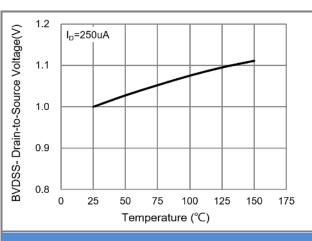


Fig.9 Threshold Voltage Variation with Temperature







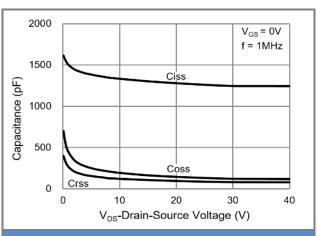
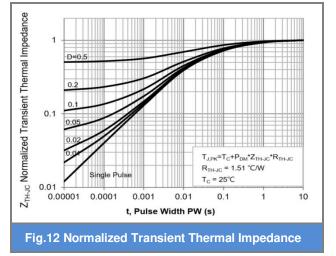


Fig.10 Capacitance vs. Drain-Source Voltage







#### Part No Packing Code Version Part No Packing Code Package Type **Packing Type** Marking Version PJQ5442\_R2\_00001 DFN5060-8L 3000pcs / 13" reel Q5442 Halogen free **Packaging Information & Mounting Pad Layout** DFN5060-8L Dimension DFN5060-8L Pad Layout Unit: inch(mm) Unit: inch(mm) 0.197(5.00) 0.189(4.80) 0.240(6.10) 0.232(5.90) 0.228(5.80) 0.224(5.70) 0.178 (4.52) 0.154 (3.91)(6.61) 0.170 (4.32) 0.260 0.043(1.10) • 0.012(0.30) 0.008(0.20) 0.002(0.05) MAX 0.024(0.61) 0.016(0.41) 4 .149(3.78) 0.024 0.043(1.10) 0.156(3.96) 0.05 0.05 (1.27) MIN. (1.27) 0.142(3.61) (0.61)0.174 ò 0 (4.42)0.028(0.71) 0.008(0.20) 0.020(0.51) ▲ 0.020(0.51) 0.002(0.06) 0.050(1.27) 0.013(0.33) BSC.



### Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.